90 學年度 國立成功大學 系 固態電子元件試題 共 1 頁 領土班招生考試 微電子工程研究所 固態電子元件試題 第 1 頁

- 1. Explain the following in brief:
 - (a) Index system for crystal planes. (5%)
 - (b) Phonon. (5%)
 - (c) Kronig-Penny model. (5%)
 - (d) Stimulated emission. (5%)
- 2. A particle with mass m is confined to a two-dimensional box of length L and width 2L.
 - (a) Find the energy values in terms of quantum numbers n_x and n_y . (15%)
 - (b) Find the lowest degenerate level. (5%)
- 3. In Si at 300K, at what donor concentration (N_D) is the probability of donor ionization equal to 90%? Assume the ionization energy of this dopant is 0.05eV, and the effective density of states in the conduction band (N_c) is $2.8\times10^{19} \text{cm}^{-3}$. (15%)
- 4. Suppose you could dope Si with any concentration of acceptors or donors. Assuming all dopants are ionized, is the least conductive silicon sample n-type, p-type, or intrinsic? Explain. (15%)
- 5. A Si p-n junction has a linearly graded junction on the n-side with $N_D = ax$ where $a = 10^{20}$ cm⁻⁴, and a uniform doping on the p-side with $N_A = 10^{16}$ cm⁻³. Suppose the depletion region width in the p-side is 0.5 μ m at zero bias. Find the following at zero bias:
 - (a) the voltage drop across the depletion region. (15%)
 - (b) the junction capacitance if area is $100\mu m^2$. (5%)
- 6. Draw the energy band diagrams of an ideal MOS diode in the following regime:
 - (a) depletion. (5%)
 - (b) inversion. (5%)